

S/N 08/903,453

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**PATENT**

Applicant: Leonard Forbes et al.

Examiner: George C. Eckert II

Serial No.: 08/903,453

Group Art Unit: 2815

Filed: July 29, 1997

Docket: 303.378US1

Title: CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS

**AMENDMENT AND RESPONSE**



Assistant Commissioner for Patents  
Washington, D.C. 20231

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Surler

Applicant has reviewed the Office Action mailed on November 23, 1999. Please amend the above-identified patent application as follows.

**IN THE CLAIMS**

Please amend the following claim:

38.(Once Amended) The [memory cell] capacitor of claim 36 wherein:  
the first conductive layer comprises polysilicon; and  
the second conductive layer comprises polysilicon.

**RECEIVED**

FEB 24 2000

Please add the following new claims:

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39.(New) The integrated circuit field effect transistor of claim 1, further comprising:  
an n+-type source region in a p-type silicon substrate;  
an n+-type drain region in the substrate;  
a channel region in the substrate between the source region and the drain region; and  
a gate isolated from the channel region by the gate insulator.

40.(New) The integrated circuit field effect transistor of claim 1, further comprising:  
an n+-type source region in a p-type silicon substrate;  
an n+-type drain region in the substrate;  
a channel region in the substrate between the source region and the drain region;  
a floating gate isolated from the channel region by the gate insulator; and  
a polysilicon control gate separated from the floating gate by a layer of insulating material.

41.(New) The integrated circuit field effect transistor of claim 2 wherein:

02/22/2000 RTSEGAYE 00000023 08903453  
02 FC:103 468.00 OP  
03 FC:102 858.00 OP